DATA SHEET



BIPOLAR ANALOG INTEGRATED CIRCUIT $\mu PC8179TK$

3 V SILICON MMIC LOW CURRENT AMPLIFIER FOR MOBILE COMMUNICATIONS

DESCRIPTION

The μ PC8179TK is a silicon monolithic integrated circuit designed as amplifier for mobile communications. This IC can realize low current consumption with external chip inductor which can not be realized on internal 50 Ω wide band matched IC. μ PC8179TK adopts 6-pin lead-less minimold package using same chip as the conventional μ PC8179TB in 6-pin super minimold.

TK suffix IC which is smaller package than TB suffix IC contributes to reduce mounting space by 50%.

This IC is manufactured using our 30 GHz fmax UHS0 (Ultra High Speed Process) silicon bipolar process.

FEATURES

Low current consumption : Icc = 4.0 mA TYP. @ Vcc = 3.0 V

• Supply voltage : Vcc = 2.4 to 3.3 V

• Excellent isolation : ISL = 43.0 dB TYP. @ f = 1.0 GHz

ISL = 42.0 dB TYP. @ f = 1.9 GHz ISL = 42.0 dB TYP. @ f = 2.4 GHz

• Power gain : $G_P = 13.5 \text{ dB TYP}$. @ f = 1.0 GHz

 $G_P = 15.5 \text{ dB TYP.} @ f = 1.9 \text{ GHz}$ $G_P = 16.0 \text{ dB TYP.} @ f = 2.4 \text{ GHz}$

• Gain 1 dB compression output power : Po (1 dB) = +2.0 dBm TYP. @ f = 1.0 GHz

Po (1 dB) = +0.5 dBm TYP. @ f = 1.9 GHzPo (1 dB) = +0.5 dBm TYP. @ f = 2.4 GHz

Operating frequency : 0.1 to 2.4 GHz (Output port LC matching)

High-density surface mounting : 6-pin lead-less minimold package (1.5 × 1.3 × 0.55 mm)

Light weight : 3 mg (Standard value)

APPLICATION

· Buffer amplifiers on 0.1 to 2.4 GHz mobile communications system

Caution: Observe precautions when handling because these devices are sensitive to electrostatic discharge.

The information in this document is subject to change without notice. Before using this document, please confirm that this is the latest version.

Document No. PU10059EJ02V0DS (2nd edition) Date Published April 2005 CP(K)

The mark ★ shows major revised points.

ORDERING INFORMATION

Part Number	Order Number	Package	Marking	Supplying Form
μPC8179TK-E2	μPC8179TK-E2-A	6-pin lead-less minimold (1511) (Pb-Free) Note	6C	Embossed tape 8 mm wide Pin 1, 6 face the perforation side of the tape
<i>µ</i> РС8179ТК-Е2	μPC8179TK-E2-A	'	6C	•

Note With regards to terminal solder (the solder contains lead) plated products (conventionally plated), contact your nearby sales office.

 $\label{lem:remark} \textbf{Remark} \ \ \textbf{To order evaluation samples, contact your nearby sales office.}$

Part number for sample order: μ PC8179TK-A

PRODUCT LINE-UP (TA = +25°C, Vcc = Vout = 3.0 V, Zs = ZL = 50 Ω)

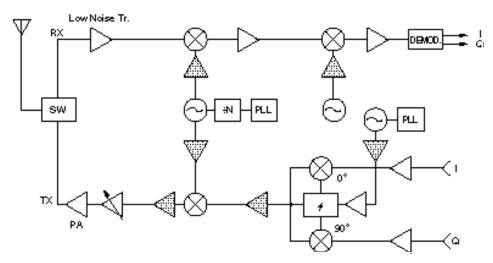
Parameter	Parameter 1.0 GHz output port matching frequency			1.66 GHz output port matching frequency		1.9 GHz output port matching frequency		2.4 GHz output port matching frequency			Marking			
Part No.	Icc (mA)	G _P (dB)	ISL (dB)	Po (1dB) (dBm)	G _P (dB)	ISL (dB)	Po (1dB) (dBm)	G _P (dB)	ISL (dB)	Po (1dB) (dBm)	G _P (dB)	ISL (dB)	Po (1dB) (dBm)	
μPC8178TB	1.9	11.0	39.0	-4.0	-	-	-	11.5	40.0	-7.0	11.5	38.0	-7.5	СЗВ
μPC8178TK	1.9	11.0	40.0	-5.5	_	-	-	11.0	41.0	-8.0	11.0	42.0	-8.0	6B
μPC8179TB	4.0	13.5	44.0	+3.0	_	-	_	15.5	42.0	+1.5	15.5	41.0	+1.0	C3C
μPC8179TK	4.0	13.5	43.0	+2.0	_	-	_	15.5	42.0	+0.5	16.0	42.0	+0.5	6C
μPC8128TB	2.8	12.5	39.0	-4.0	13.0	39.0	-4.0	13.0	37.0	-4.0	-	-	-	C2P
μPC8151TB	4.2	12.5	38.0	+2.5	15.0	36.0	+1.5	15.0	34.0	+0.5	ı	_	_	C2U
μPC8152TB	5.6	23.0	40.0	-4.5	19.5	38.0	-8.5	17.5	35.0	-8.5	ı	_	_	C2V

Remarks 1. Typical performance. Please refer to ELECTRICAL CHARACTERISTICS in detail.

2. To know the associated product, please refer to each latest data sheet.

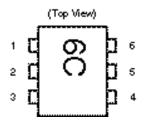
SYSTEM APPLICATION EXAMPLE

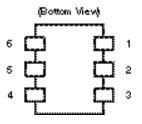
Location examples in digital cellular



These ICs can be added to your system around $\underline{\mathbb{A}}$ parts, when you need more isolation or gain. The application herein, however, shows only examples, therefore the application can depend on your kit evaluation.

PIN CONNECTIONS





Pin No.	Pin Name
1	INPUT
2	GND
3	GND
4	OUTPUT
5	GND
6	Vcc

PIN EXPLANATION

Pin No.	Pin Name	Applied Voltage (V)	Pin Voltage (V)	Function and Applications	Internal Equivalent Circuit
1	INPUT	-	0.90	Signal input pin. A internal matching circuit, configured with resisters, enables $50~\Omega$ connection over a wide band. This pin must be coupled to signal source with capacitor for DC cut.	
2 3 5	GND	0	-	Ground pin. This pin should be connected to system ground with minimum inductance. Ground pattern on the board should be formed as wide as possible. All the ground pins must be connected together with wide ground pattern to decrease impedance defference.	(a) (b) (c) (c) (c) (c) (c) (c) (c) (c) (c) (c
4	OUTPUT	Voltage as same as Vcc through external inductor	-	Signal output pin. This pin is designed as collector output. Due to the high impedance output, this pin should be externally equipped with LC matching circuit to next stage. For L, a size 1 005 chip inductor can be chosen.	3 1 6
6	Vcc	2.4 to 3.3	-	Power supply pin. This pin should be externally equipped with bypass capacitor to minimize its impedance.	

Note Pin voltage is measured at Vcc = 3.0 V.

ABSOLUTE MAXIMUM RATINGS

Parameter	Symbol	Test Conditions	Ratings	Unit
Supply Voltage	Vcc	T _A = +25°C, Pin 4, Pin 6	3.6	V
Circuit Current	Icc	T _A = +25°C	15	mA
Power Dissipation	Po	T _A = +85°C Note	232	mW
Operating Ambient Temperature	TA		-40 to +85	°C
Storage Temperature	Tstg		−55 to +150	°C
Input Power	Pin	T _A = +25°C	+5	dBm

Note Mounted on double-sided copper-clad $50 \times 50 \times 1.6$ mm epoxy glass PWB

RECOMMENDED OPERATING RANGE

Parameter	Symbol	MIN.	TYP.	MAX.	Unit	Remarks
Supply Voltage	Vcc	2.4	3.0	3.3	V	The same voltage should be applied to pin 4 and pin 6.
Operating Ambient Temperature	TA	-40	+25	+85	°C	

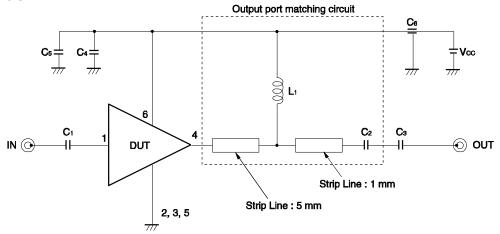
ELECTRICAL CHARACTERISTICS

(Unless otherwise specified, $T_A = +25$ °C, $V_{CC} = V_{Out} = 3.0 \text{ V}$, $Z_S = Z_L = 50 \Omega$, at LC matched frequency)

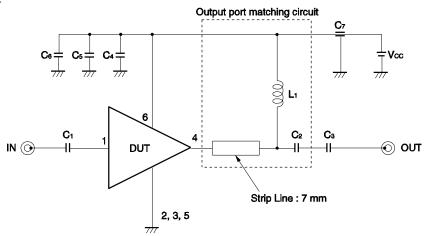
Parameter	Symbol	Test Conditions	MIN.	TYP.	MAX.	Unit
Circuit Current	Icc	No signal	2.9	4.0	5.4	mA
Power Gain	G₽	f = 1.0 GHz, Pin = -30 dBm	11.0	13.5	15.5	dB
		f = 1.9 GHz, P _{in} = -30 dBm	13.0	15.5	17.5	
		f = 2.4 GHz, Pin = -30 dBm	14.0	16.0	18.5	
Isolation	ISL	f = 1.0 GHz, Pin = -30 dBm	39.0	43.0	-	dB
		f = 1.9 GHz, Pin = -30 dBm	37.0	42.0	_	
		f = 2.4 GHz, Pin = -30 dBm	37.0	42.0	_	
Gain 1 dB Compression Output	Po (1 dB)	f = 1.0 GHz	-0.5	+2.0	_	dBm
Power		f = 1.9 GHz	-2.0	+0.5	_	
		f = 2.4 GHz	-3.0	+0.5	_	
Noise Figure	NF	f = 1.0 GHz	-	5.0	6.5	dB
		f = 1.9 GHz	-	5.0	6.5	
		f = 2.4 GHz	ı	5.0	6.5	
Input Return Loss	RLin	f = 1.0 GHz, Pin = -30 dBm	4.0	7.0	-	dB
		f = 1.9 GHz, Pin = -30 dBm	4.0	7.0	-	
		f = 2.4 GHz, Pin = -30 dBm	6.0	9.0	_	

TEST CIRCUITS

<1> f = 1.0 GHz



<2> f = 1.9 GHz



<3> f = 2.4 GHz

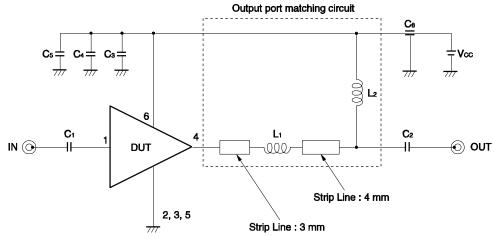
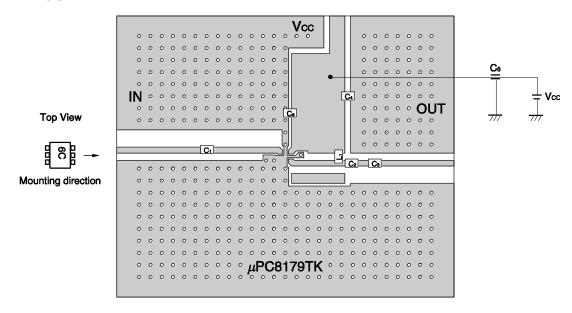


ILLUSTRATION OF THE TEST CIRCUIT ASSEMBLED ON EVALUATION BOARD

<1> f = 1.0 GHz



Remarks 1. $42 \times 35 \times 0.4$ mm double-sided copper-clad polyimide board

2. Back side: GND pattern

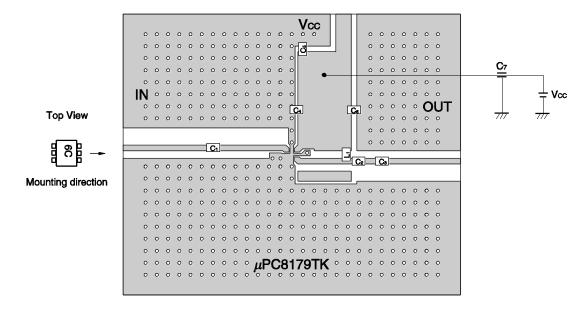
3. Gold plated on pattern

4. o:Through holes

COMPONENT LIST

Form	Symbol	Value	Type code	Maker
Chip capacitor	C ₁ , C ₃	1 000 pF	GRM40CH102J50PT	murata
	C ₂	0.75 pF	GRM39CKR75C50PT	murata
	C4	5 pF	GRM39CH050C50PT	murata
	C ₅	8 pF	GRM39CH080D50PT	murata
Feed-though Capacitor	C ₆	1 000 pF	DFT301-801 × 7R102S50	murata
Chip inductor	L ₁	12 nH	LL1608-FH12N	TOKO

<2> f = 1.9 GHz



Remarks 1. $42 \times 35 \times 0.4$ mm double-sided copper-clad polyimide board

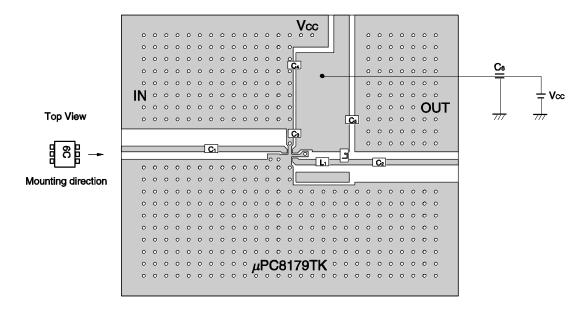
Back side: GND pattern
 Gold plated on pattern

4. o:Through holes

COMPONENT LIST

Form	Symbol	Value	Type code	Maker
Chip capacitor	C ₁ , C ₃ , C ₅ , C ₆ 1 000 pF GRM		GRM40CH102J50PT	murata
	C ₂	0.5 pF	GRM39CKR5C50PT	murata
	C ₄	8 pF	GRM39CH080D50PT	murata
Feed-though Capacitor	C 7	1 000 pF	DFT301-801 × 7R102S50	murata
Chip inductor	L ₁	2.7 nH	LL1608-FH2N7S	токо

<3> f = 2.4 GHz



Remarks 1. $42 \times 35 \times 0.4$ mm double-sided copper-clad polyimide board

Back side: GND pattern
 Gold plated on pattern

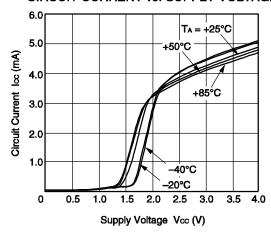
4. o:Through holes

COMPONENT LIST

Form	Symbol	Value	Type code	Maker
Chip capacitor	C1, C2, C4, C5	1 000 pF	GRM40CH102J50PT	murata
	Сз	10 pF	GRM39CH100D50PT	murata
Feed-though Capacitor	C ₆	1 000 pF	DFT301-801 × 7R102S50	murata
Chip inductor	L ₁	2.7 nH	LL1608-FH2N7S	токо
	L ₂	1.8 nH	LL1608-FH1N8S	TOKO

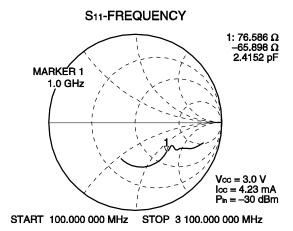
■ TYPICAL CHARACTERISTICS (T_A = +25°C, unless otherwise specified)

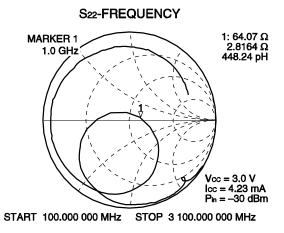
CIRCUIT CURRENT vs. SUPPLY VOLTAGE

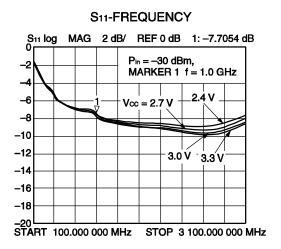


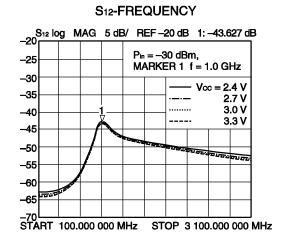
Remark The graph indicates nominal characteristics.

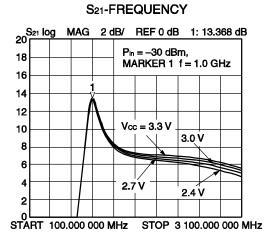
f = 1.0 GHz MATCHING

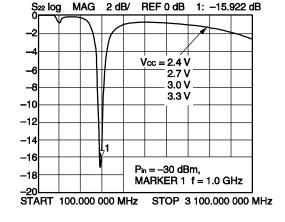








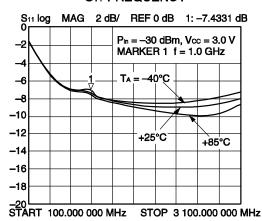




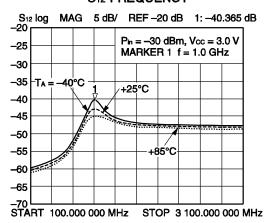
S22-FREQUENCY

Remark The graphs indicate nominal characteristics.

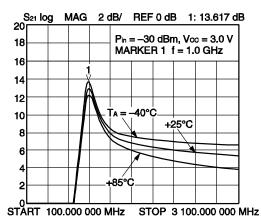
S₁₁-FREQUENCY



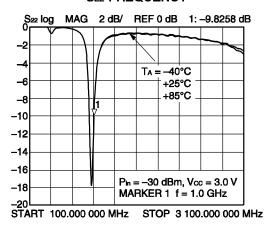
S₁₂-FREQUENCY



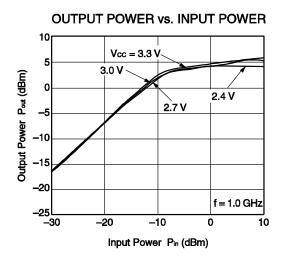
S21-FREQUENCY

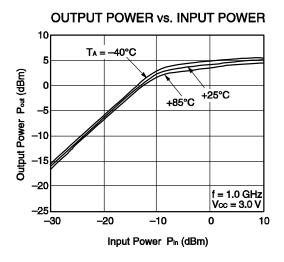


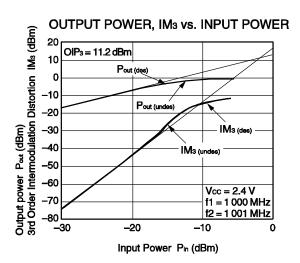
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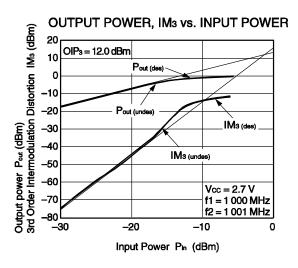


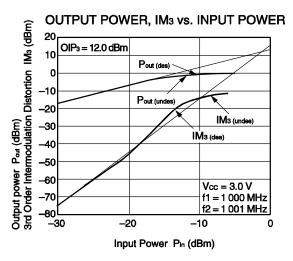
Remark The graphs indicate nominal characteristics.

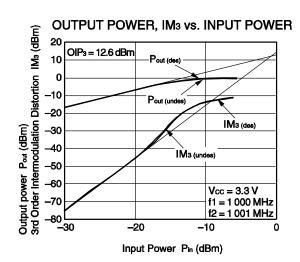




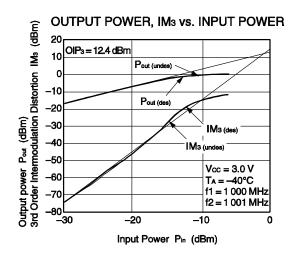


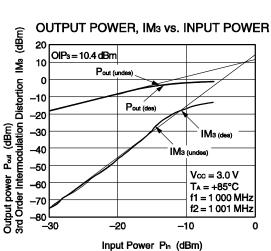


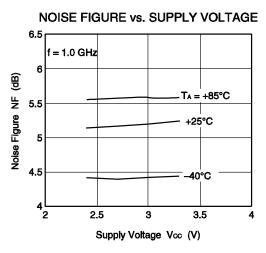




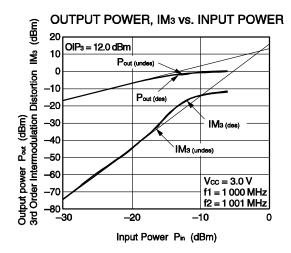
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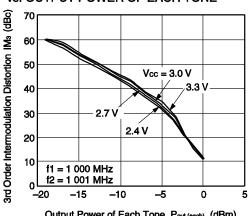




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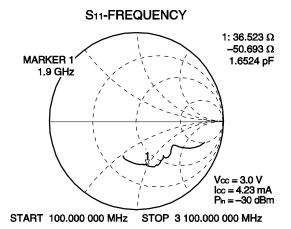


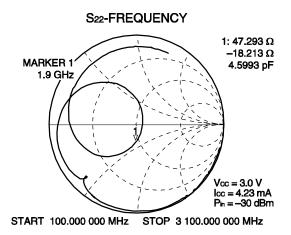
3RD ORDER INTERMODULATION DISTORTION vs. OUTPUT POWER OF EACH TONE

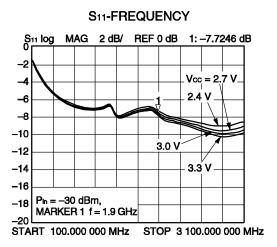


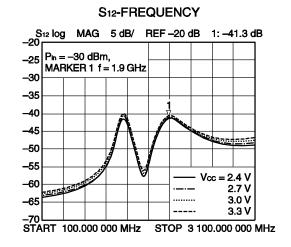
Output Power of Each Tone Pout (each) (dBm)

f = 1.9 GHz MATCHING









S22-FREQUENCY

REF 0 dB

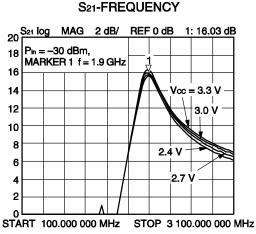
1: -15.331 dB

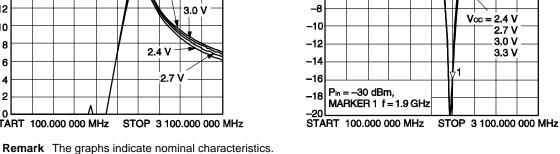
2 dB/

MAG

S₂₂ log

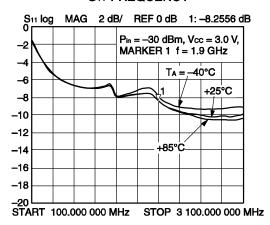
-6



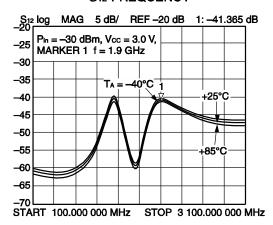


15

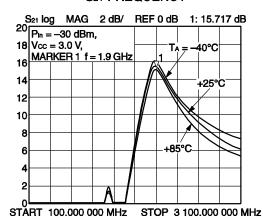
S₁₁-FREQUENCY



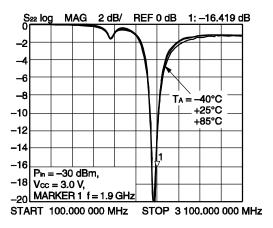
S₁₂-FREQUENCY



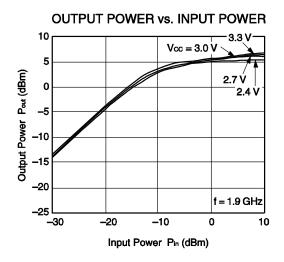
S21-FREQUENCY

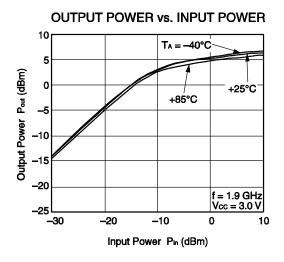


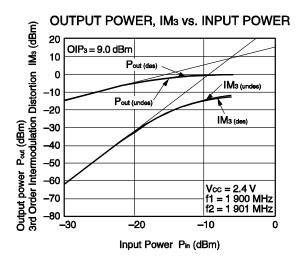
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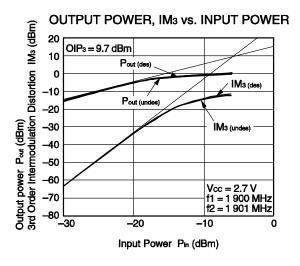


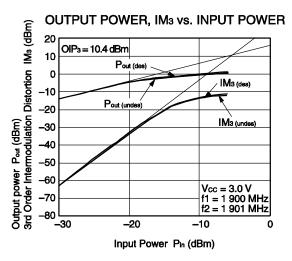
Remark The graphs indicate nominal characteristics.

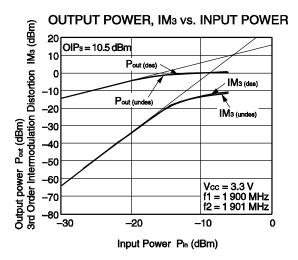




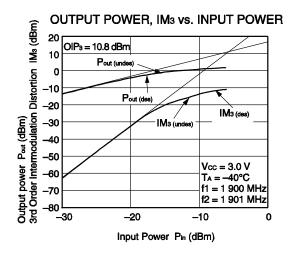


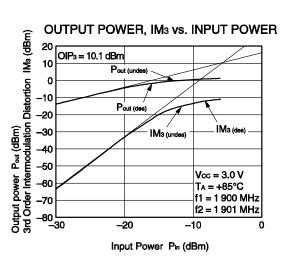


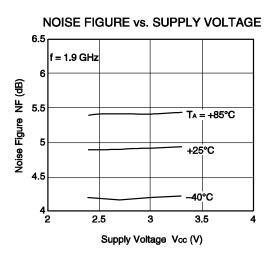




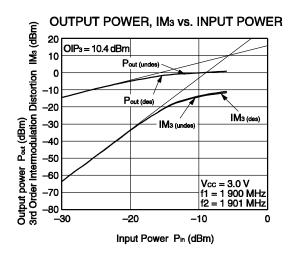
Remark The graphs indicate nominal characteristics.



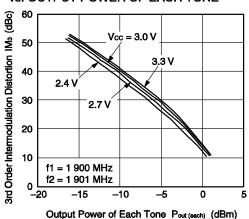




Remark The graphs indicate nominal characteristics.

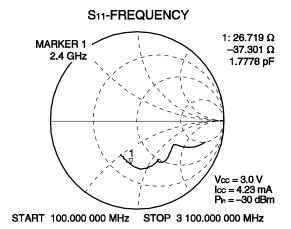


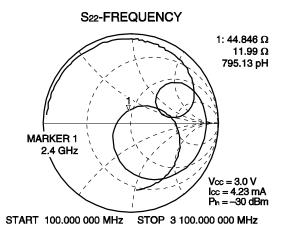
3RD ORDER INTERMODULATION DISTORTION vs. OUTPUT POWER OF EACH TONE

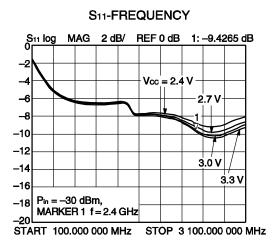


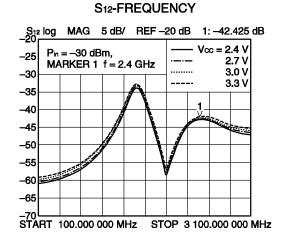
18

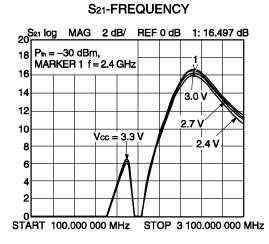
f = 2.4 GHz MATCHING

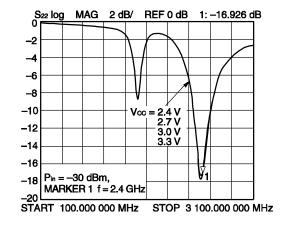








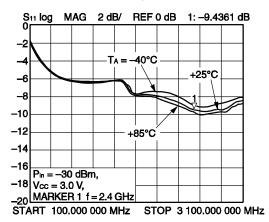




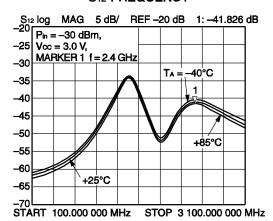
S22-FREQUENCY

Remark The graphs indicate nominal characteristics.

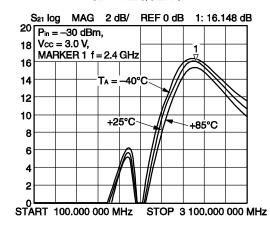
S₁₁-FREQUENCY



S₁₂-FREQUENCY

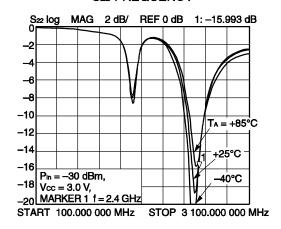


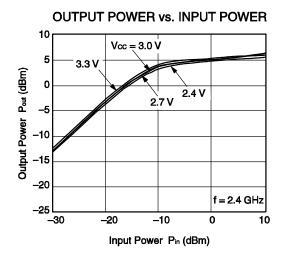
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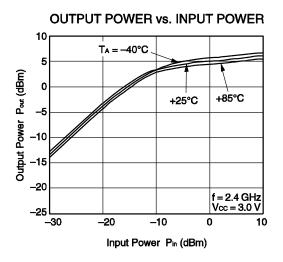


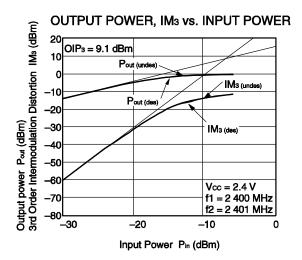
Remark The graphs indicate nominal characteristics.

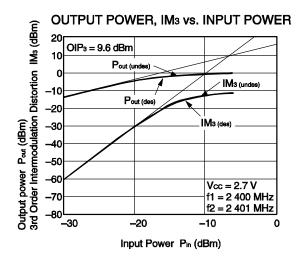
S22-FREQUENCY

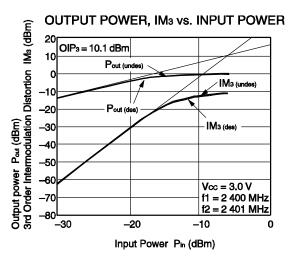


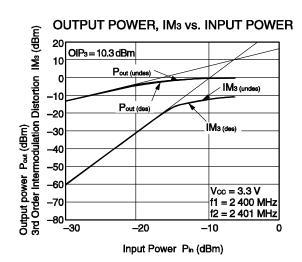




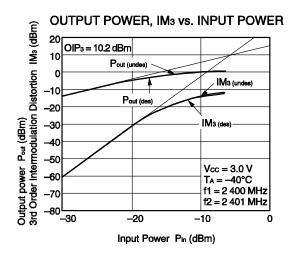


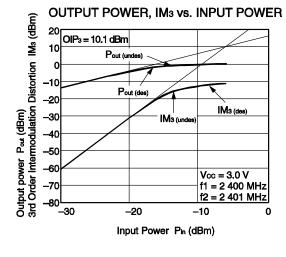


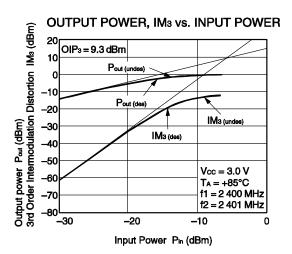




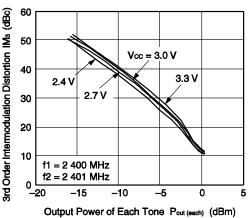
Remark The graphs indicate nominal characteristics.

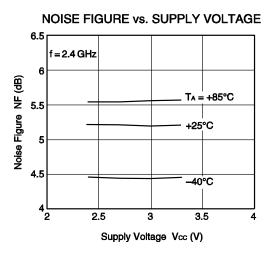










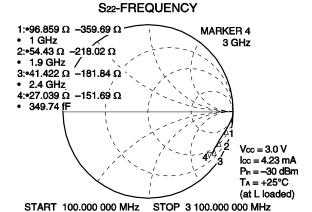


Remark The graphs indicate nominal characteristics.

f = 3.0 GHz MATCHING

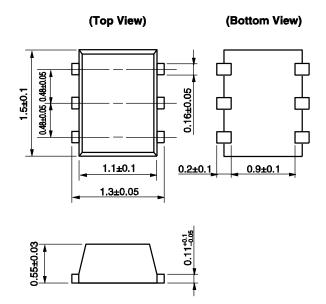
S11-FREQUENCY1:•77.02 Ω -65.883 Ω MARKER 4 • 1 GHz 2:•37.43 Ω -53.027 Ω • 1.9 GHz 3:•28.781 Ω -39.209 Ω • 2.4 GHz/ 4:•25.676 Ω -27.78 Ω • 1.9097 pF Vcc = 3.0 Vlcc = 4.23 mA Pn = -30 dBm $Ta = +25^{\circ}C$ (at L loaded) START 100.000 000 MHz STOP 3 100.000 000 MHz

Remark The graphs indicate nominal characteristics.



■ PACKAGE DIMENSIONS

6-PIN LEAD-LESS MINIMOLD (1511) (UNIT: mm)



NOTE ON CORRECT USE

- (1) Observe precautions for handling because of electro-static sensitive devices.
- (2) Form a ground pattern as widely as possible to minimize ground impedance (to prevent undesired oscillation). All the ground pins must be connected together with wide ground pattern to decrease impedance difference.
- (3) The bypass capacitor should be attached to Vcc line.
- (4) The inductor (L) should be attached between output and Vcc pins. The L and series capacitor (C) values should be adjusted for applied frequency to match impedance to next stage.
- (5) The DC capacitor must be attached to input pin.

RECOMMENDED SOLDERING CONDITIONS

This product should be soldered and mounted under the following recommended conditions. For soldering methods and conditions other than those recommended below, contact your nearby sales office.

Soldering Method	Soldering Conditions	Condition Symbol	
Infrared Reflow	Peak temperature (package surface temperature) Time at peak temperature Time at temperature of 220°C or higher Preheating time at 120 to 180°C Maximum number of reflow processes Maximum chlorine content of rosin flux (% mass)	: 260°C or below : 10 seconds or less : 60 seconds or less : 120±30 seconds : 3 times : 0.2%(Wt.) or below	IR260
Wave Soldering	Peak temperature (molten solder temperature) Time at peak temperature Preheating temperature (package surface temperature) Maximum number of flow processes Maximum chlorine content of rosin flux (% mass)	: 260°C or below : 10 seconds or less : 120°C or below : 1 time : 0.2%(Wt.) or below	WS260
Partial Heating	Peak temperature (terminal temperature) Soldering time (per side of device) Maximum chlorine content of rosin flux (% mass)	: 350°C or below : 3 seconds or less : 0.2%(Wt.) or below	HS350

Caution Do not use different soldering methods together (except for partial heating).

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 and industrial robots
 - "Special": Transportation equipment (automobiles, trains, ships, etc.), traffic control systems, anti-disaster
 systems, anti-crime systems, safety equipment and medical equipment (not specifically designed
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M8E 00.4-0110

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